Atty Docket No. 30203/37708 .

Title: Magnetic Random Access Memory Having
Transistor of Vertical Structure with Writing Line Formed
on an Upper Portion of the Magnetic Tunnel Junction Cell
Inventor: Cha
Figure 1
Sheet 1 of 6

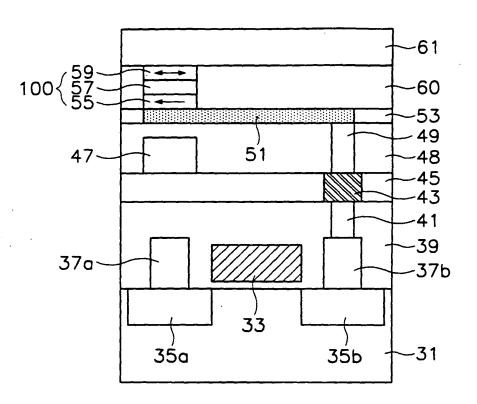


Fig.1 (Prior Art)

Title: Magnetic Random Access Memory Having Transistor of Vertical Structure with Writing Line Formed on an Upper Portion of the Magnetic Tunnel Junction Cell Inventor: Cha Figure 2A Sheet 2 of 6

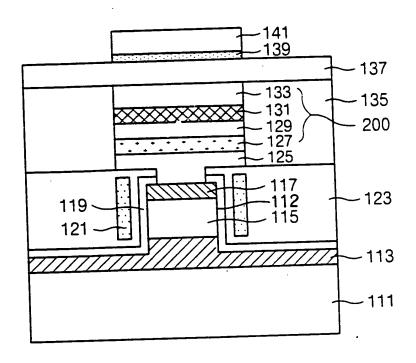


Fig.2A

Atty Docket No.: 30205/37980A
Title: Magnetic Random Access Memory Having
Transistor of Vertical Structure with Writing Line Formed
on an Upper Portion of the Magnetic Tunnel Junction Cell
Inventor: Cha
Figures 2B and 2C
Sheet 3 of 6

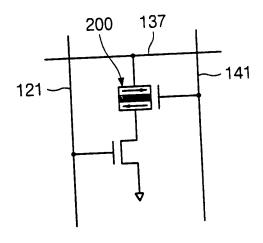


Fig.2B

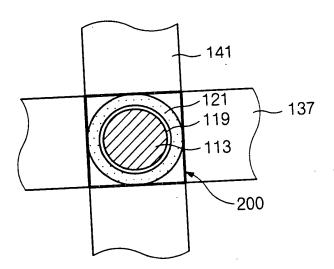


Fig.2C

Atty Docket No. 30203/3 200
Title: Magnetic Random Access Memory Having
Transistor of Vertical Structure with Writing Line Formed
on an Upper Portion of the Magnetic Tunnel Junction Cell
Inventor: Cha
Figure 3
Sheet 4 of 6

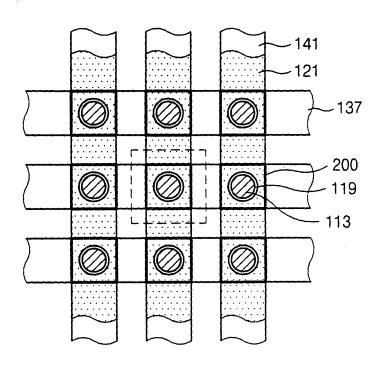


Fig.3

Atty Docket No.: 30205/37980A
Title: Magnetic Random Access Memory Having
Transistor of Vertical Structure with Writing Line Formed
on an Upper Portion of the Magnetic Tunnel Junction Cell
Inventor: Cha
Figure 4
Sheet 5 of 6

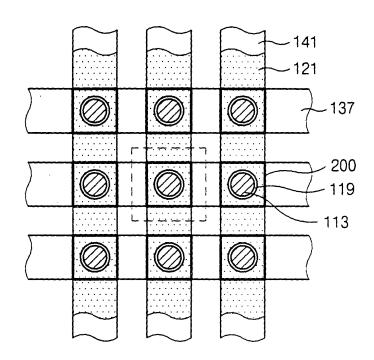


Fig.4

Atty Docket No. 302007373007

Title: Magnetic Random Access Memory Having
Transistor of Vertical Structure with Writing Line Formed
on an Upper Portion of the Magnetic Tunnel Junction Cell
Inventor: Cha
Figure 5

Sheet 6 of 6

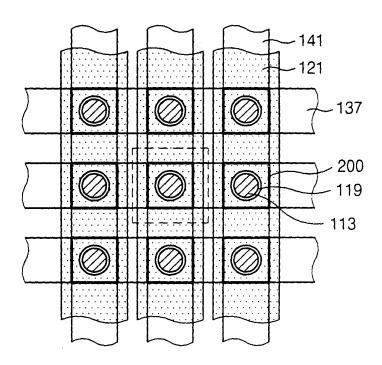


Fig.5